1. Record Nr. UNINA9910828359203321

Autore	Louw Bill
Titolo	Corpus stylistics as contextual prosodic theory and subtext / / Bill Louw, Marija Milojkovic
Pubbl/distr/stampa	Amsterdam, Netherlands ; ; Philadelphia, Pennsylvania : , : John Benjamins Publishing Company, , 2016 ©2016
Descrizione fisica	1 online resource (441 p.)
Collana	Linguistic Approaches to Literature, , 1569-3112 ; ; Volume 23
Disciplina	401/.43
Soggetti	Semantic prosody English language - Discourse analysis - Data processing English language - Variation - Data processing Thought and thinking - Data processing
Lingua di pubblicazione	Inglese
Formato	Materiale a stampa
Livello bibliografico	Monografia
Note generali	Description based upon print version of record.
Nota di bibliografia	Includes bibliographical references and index.
Nota di contenuto	Part I: Theoretical considerations from the beginnings to the present day -- Chapter 1: Delexicalisation, relexicalisation and classroom application -- Chapter 2: collocation, interpretation, and context of situation -- Chapter 3: Semantic prosodies, irony, insincerity and literary analysis -- Chapter 4: Data-assisted negotiating -- Chapter 5: The analysis and creation of humour -- Chapter 6: Events in the context of culture, language events, subtext -- PART II: New applications -- Chapter 7: Alexander Pushkin and authorial intention -- Chapter 8: Translating Pushkin: a case in point -- Chapter 11 : Contextualprosodic theory in the stylistics classroom --Chapter 12: Student-centred stylistics: does subtext read text?.

2. Record Nr. UNINA9910557343303321

Autore	Piotrowska Anna B
Titolo	Micro- and Nanotechnology of Wide Bandgap Semiconductors
Pubbl/distr/stampa	Basel, Switzerland, : MDPI - Multidisciplinary Digital Publishing Institute, 2021
Descrizione fisica	1 online resource (114 p.)
Soggetti	Technology: general issues
Lingua di pubblicazione	Inglese
Formato	Materiale a stampa
Livello bibliografico	Monografia

Sommario/riassunto

Owing to their unique characteristics, direct wide bandgap energy, large breakdown field, and excellent electron transport properties, including operation at high temperature environments and low sensitivity to ionizing radiation, gallium nitride (GaN) and related group III-nitride heterostructures proved to be enabling materials for advanced optoelectronic and electronic devices and systems. Today, they are widely used in high performing short wavelength light emitting diodes (LEDs) and laser diodes (LDs), high performing radar, wireless telecommunications, as well 'green' power electronics. Impressive progress in GaN technology over the last 25 years has been driven by a continuously growing need for more advanced systems, and still new challenges arise and need to be solved. Actually, lighting industry, RF defene industry, and 5G mmWave telecommunication systems are driving forces for further intense research in order to reach full potential of GaN-based semiconductors. In the literature, there is a number of review papers and publications reporting technology progress and indicating future trends. In this Special Issue of Electronics, eight papers are published, the majority of them focusing materials and process technology of GaN-based devices fabricated on native GaN substrates. The specific topics include: GaN single crystalline substrates for electronic devices by ammonothermal and HVPE methods, Selective - Area Metalorganic Vapour - Phase Epitaxy of GaN and AlGaN/GaN hetereostructures for HEMTs, Advances in Ion

Implantation of GaN and Related Materials including high pressure processing (lattice reconstruction) of ion implanted GaN (Mg and Be) and III-Nitride Nanowires for electronic and optoelectronic devices.